

140 COMMERCE DRIVE MONTGOMERYVILLE, PA 18936-1013

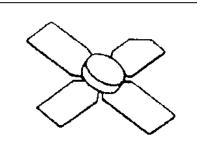
PHONE: (215) 631-9840 FAX: (215) 631-9855

SD1420-01

RF AND MICROWAVE TRANSISTORS 800-900 MHz BASE STATION APPLICATIONS

Features

- 860 960 MHz
- 24 VOLTS
- COMMON EMITTER
- GOLD METALLIZATION
- CLASS A LINEAR OPERATION
- P_{OUT} = 0.9 W MIN.
- 9.5 dB GAIN



.280 4LSL (M123) epoxy sealed

PIN CONNECTION 1 1 2 1. Collector 3. Base 2. Emitter 4. Emitter

DESCRIPTION:

The SD1420-01 is a gold metallized epitaxial silicon NPN planar transistor designed for high-linearity Class A operation Cellular Base Station applications. The SD1420-01 is also available in a stud package as the SD1420.

ABSOLUTE MAXIMUM RATINGS (Tcase = 25°C)

Symbol	Parameter	Value	Unit
V _{CBO}	Collector-Base Voltage	40	V
V _{CEO}	Collector-Emitter Voltage	28	V
V _{EBO}	Emitter-Base Voltage	3.5	V
Ic	Device Current	.250	Α
P _{DISS}	Power Dissipation	7	W
TJ	Junction Temperature	+ 200	°C
T _{STG}	Storage Temperature	-55 to +150	°C

THERMAL DATA

R _{TH(j-c)}	Junction-Case Thermal Resistance	20	°C/W
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ELECTRICAL SPECIFICATIONS (Tcase = 25°C)

STATIC

Symbol	Test Conditions		Value		
	Test Conditions	Min.	Тур.		
BV _{CBO}	I _C = 1 mA	40			V
BV _{CEO}	I _C = 1 mA	28			٧
BV _{EBO}	I _E = 1 mA	3.5			٧
I _{CES}	V _{CB} = 24 V			.5	mA
h _{FE}	$V_{CE} = 5 V$ $I_C = .1 A$	20		120	

DYNAMIC

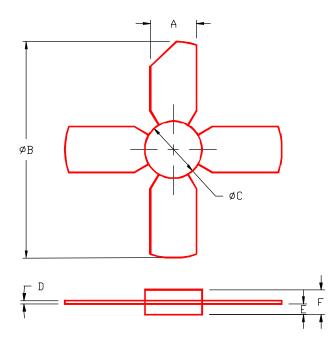
Ob-al		Took Comeli	ition o		Value		Haita
Symbol		Test Cond	itions	Min.	Тур.	Max.	Units W
P _{out}	f = 960 MHz	V _{CE} = 24 V	I _{CQ} = 200 mA	2.1			W
G _P	f = 960 MHz	V _{CE} = 24 V	I _{CQ} = 125 mA	8.9	9.0		dB
Сов	f = 1 MHz	V _{CB} = 28 V				5.0	pF



SD1420-01

PACKAGE MECHANICAL DATA

PACKAGE STYLE M123



	MINIMUM	MAXIMUM	MINIMUM	MUMIXAM
	INCHES/MM	INCHES/MM	[NCHES/MM	INCHES/MM
Α	.220/5,59	.230/5,84		
В		1.055/26,8		
С	.275/6,99	.285/7,24		
D	.004/0,10	.006/0,15		
Ε	.050/1,27	.060/1,52		
F	.118/3,00	.130/3,30		